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Pages 1 to 49

**INTEGRATED CIRCUITS, SILICON MONOLITHIC,
CMOS 8-INPUT NAND/AND GATE,
BASED ON TYPE 4068B**

ESA/SCC Detail Specification No. 9201/061



**space components
coordination group**

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**SCC**

ESA/SCC Detail Specification

No. 9201/061

PAGE 2

ISSUE 3

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
		This Issue supersedes Issue 2 and incorporates all modifications defined in Revisions 'A', 'B' and 'C' to Issue 2 and the changes agreed in the following DCRs:-		
		Cover page		None
		DCN		None
		Para. 1.3	: New sentence added	221602
		Table 1(b)	: No. 8, Maximum temperature amended	221602
		Para. 4.8.6	: Last sentence deleted, new text added	221602
		Appendix 'A'	: Appendix added	221602

**SCC**ESA/SCC Detail Specification
No. 9201/061

PAGE 3

ISSUE 3

TABLE OF CONTENTS

	<u>Page</u>
1. <u>GENERAL</u>	5
1.1 Scope	5
1.2 Component Type Variants	5
1.3 Maximum Ratings	5
1.4 Parameter Derating Information	5
1.5 Physical Dimensions	5
1.6 Pin Assignment	5
1.7 Truth Table	5
1.8 Circuit Schematic	5
1.9 Functional Diagram	5
1.10 Handling Precautions	5
1.11 Input Protection Network	5
2. <u>APPLICABLE DOCUMENTS</u>	16
3. <u>TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS</u>	16
4. <u>REQUIREMENTS</u>	16
4.1 General	16
4.2 Deviations from Generic Specification	16
4.2.1 Deviations from Special In-process Controls	16
4.2.2 Deviations from Final Production Tests	16
4.2.3 Deviations from Burn-in Tests	16
4.2.4 Deviations from Qualification Tests	17
4.2.5 Deviations from Lot Acceptance Tests	17
4.3 Mechanical Requirements	17
4.3.1 Dimension Check	17
4.3.2 Weight	17
4.4 Materials and Finishes	17
4.4.1 Case	17
4.4.2 Lead Material and Finish	17
4.5 Marking	17
4.5.1 General	17
4.5.2 Lead Identification	17
4.5.3 The SCC Component Number	18
4.5.4 Traceability Information	18
4.6 Electrical Measurements	18
4.6.1 Electrical Measurements at Room Temperature	18
4.6.2 Electrical Measurements at High and Low Temperatures	18
4.6.3 Circuits for Electrical Measurements	18
4.7 Burn-in Tests	18
4.7.1 Parameter Drift Values	18
4.7.2 Conditions for H.T.R.B. and Burn-in	18
4.7.3 Electrical Circuits for H.T.R.B. and Burn-in	18
4.8 Environmental and Endurance Tests	46
4.8.1 Electrical Measurements on Completion of Environmental Tests	46
4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests	46
4.8.3 Electrical Measurements on Completion of Endurance Tests	46
4.8.4 Conditions for Operating Life Test	46
4.8.5 Electrical Circuits for Operating Life Tests	46
4.8.6 Conditions for High Temperature Storage Test	46

**TABLES**Page

1(a)	Type Variants	6
1(b)	Maximum Ratings	6
2	Electrical Measurements at Room Temperature, d.c. Parameters	19
	Electrical Measurements at Room Temperature, a.c. Parameters	24
3(a)	Electrical Measurements at High Temperature	26
3(b)	Electrical Measurements at Low Temperature	30
4	Parameter Drift Values	41
5(a)	Conditions for Burn-in High Temperature Reverse Bias, N-Channels	42
5(b)	Conditions for Burn-in High Temperature Reverse Bias, P-Channels	42
5(c)	Conditions for Burn-in Dynamic	43
6	Electrical Measurements on Completion of Environmental Tests and at Intermediate Points and on Completion of Endurance Testing	47

FIGURES

1	Not applicable	
2	Physical Dimensions	7
3(a)	Pin Assignment	12
3(b)	Truth Table	13
3(c)	Circuit Schematic	14
3(d)	Functional Diagram	15
3(e)	Input Protection Network	15
4	Circuits for Electrical Measurements	34
5(a)	Electrical Circuit for Burn-in High Temperature Reverse Bias, N-Channels	44
5(b)	Electrical Circuit for Burn-in High Temperature Reverse Bias, P-Channels	44
5(c)	Electrical Circuit for Burn-in Dynamic	45

APPENDICES (Applicable to specific Manufacturers only)

'A'	Agreed Deviations for STMicroelectronics (F)	49
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**1. GENERAL****1.1 SCOPE**

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, CMOS 8-Input NAND/AND Gate, having fully buffered outputs, based on Type 4068B. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the applicable ESA/SCC Generic Specification.

1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

1.5 PHYSICAL DIMENSIONS

As per Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 TRUTH TABLE

As per Figure 3(b).

1.8 CIRCUIT SCHEMATIC

As per Figure 3(c).

1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).

1.10 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling. These components are Categorised as Class 1 with a Minimum Critical Path Failure Voltage of 400Volts.

1.11 INPUT PROTECTION NETWORK

Double diode protection shall be incorporated into each input as shown in Figure 3(e).



TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	G2 or G8
02	FLAT	2(a)	G4
03	D.I.L.	2(b)	G2 or G8
04	D.I.L.	2(b)	G4
07	CHIP CARRIER	2(c)	2
08	SO CERAMIC	2(d)	G2
09	SO CERAMIC	2(d)	G4

TABLE 1(b) - MAXIMUM RATINGS

NO.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNITS	REMARKS
1	Supply Voltage	V_{DD}	-0.5 to +18	V	Note 1
2	Input Voltage	V_{IN}	-0.5 to $V_{DD} + 0.5$	V	Note 2 Power on
3	D.C. Input Current	$\pm I_{IN}$	10	mA	-
4	D.C. Output Current	$\pm I_O$	10	mA	Note 3
5	Device Dissipation	P_D	200	mWdc	Per Package
6	Output Dissipation	P_{DSO}	100	mWdc	Note 4
7	Operating Temperature Range	T_{op}	-55 to +125	°C	-
8	Storage Temperature Range	T_{stg}	-65 to +150	°C	-
9	Soldering Temperature For FP and DIP For CCP	T_{sol}	+300 +245	°C	Note 5 Note 6

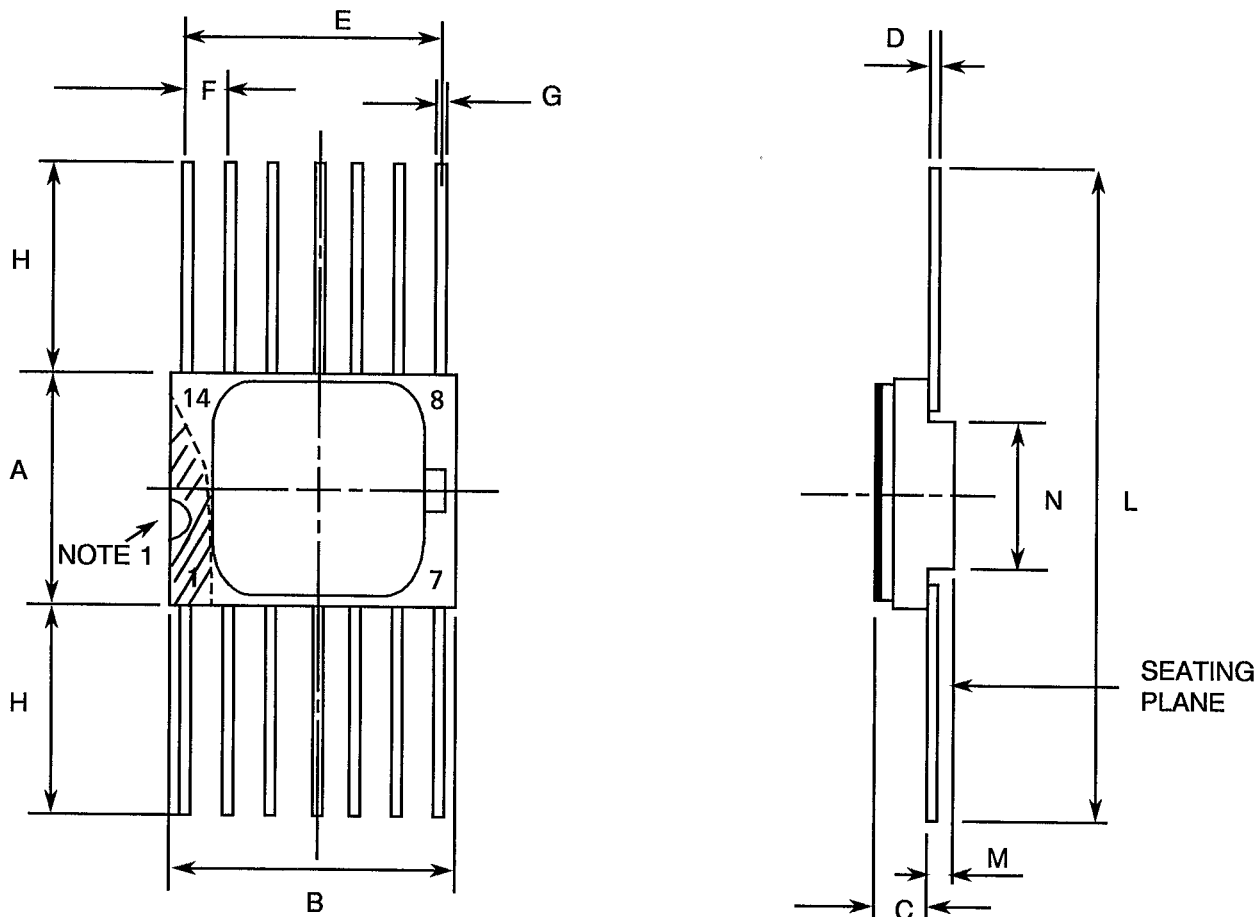
NOTES

1. Device is functional from +3V to +15V with reference to V_{SS} .
2. $V_{DD} + 0.5V$ should not exceed +18V.
3. The maximum output current of any single output.
4. The maximum power dissipation of any single output.
5. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
6. Duration 30 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.



FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - FLAT PACKAGE, 14-Pin



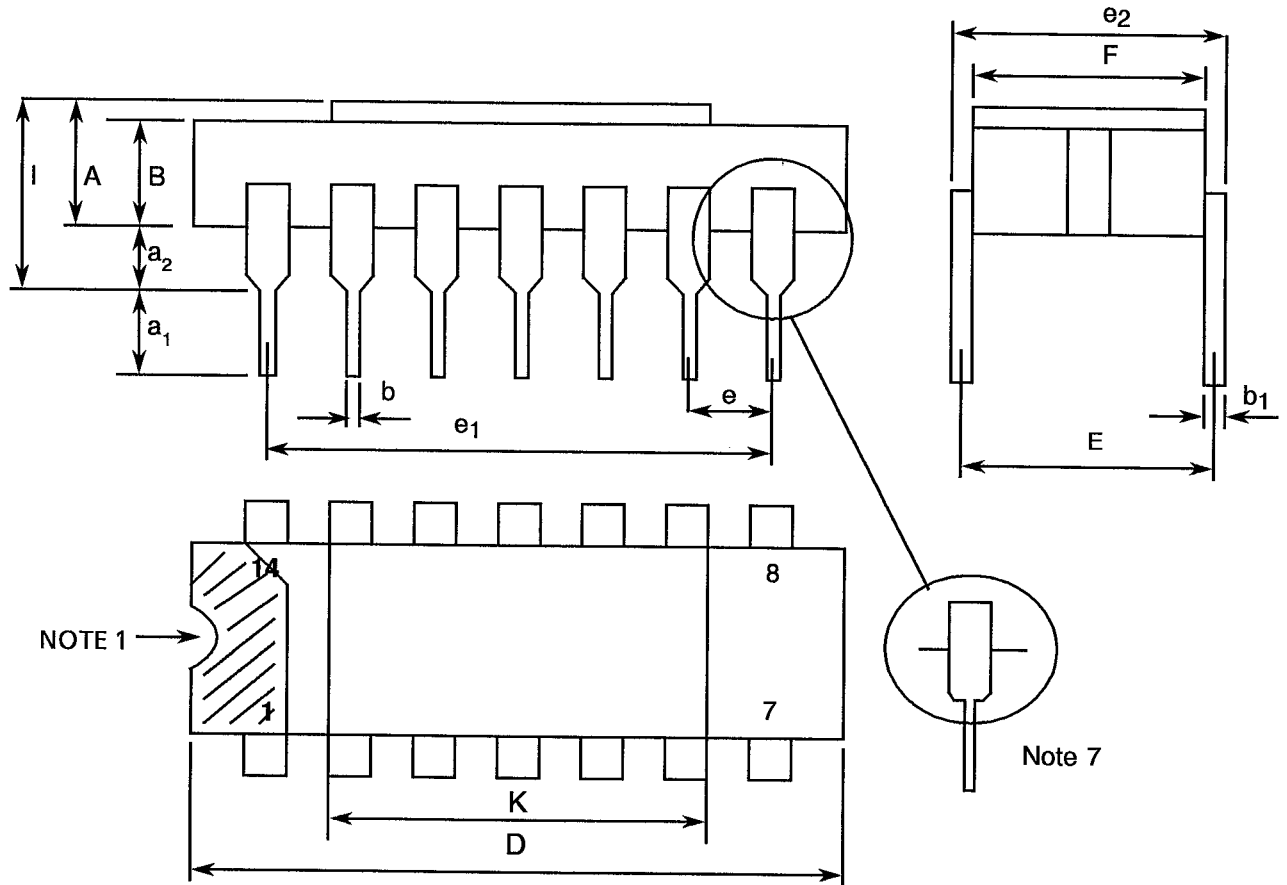
SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	6.75	7.06	
B	9.76	10.14	
C	1.49	1.95	
D	0.102	0.152	3
E	7.50	7.75	
F	1.27	TYPICAL	4
G	0.38	0.48	3
H	6.0	-	3
L	18.75	22.0	
M	0.33	0.43	
N	4.31	TYPICAL	

NOTES: See Page 11.



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - DUAL-IN-LINE PACKAGE, 14-PIN



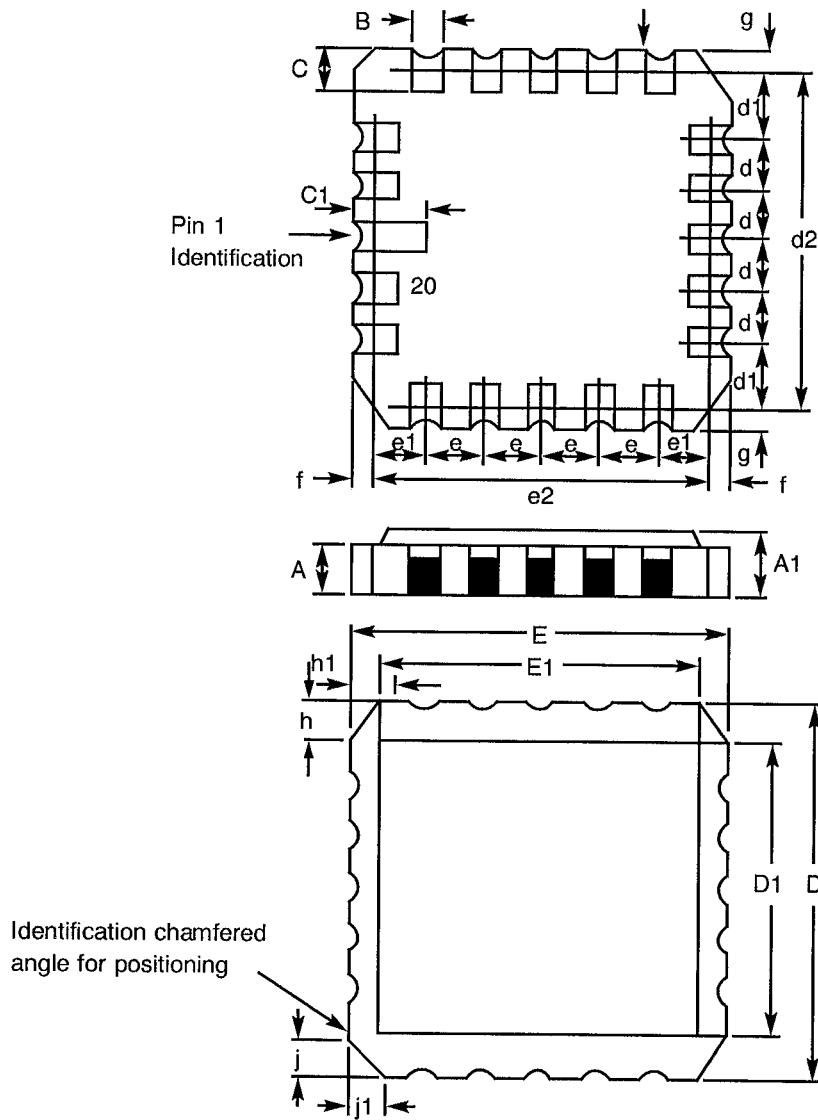
SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	2.10	2.54	
a ₁	3.0	3.7	
a ₂	0.63	1.14	2
B	1.82	2.23	
b	0.40	0.50	3
b ₁	0.20	0.30	3
D	18.79	19.20	
E	7.36	7.87	
e	2.29	2.79	4
e ₁	15.11	15.37	
e ₂	7.62	8.12	
F	7.11	7.75	
I	-	3.70	
K	10.90	12.10	

NOTES: See Page 11.



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - CHIP CARRIER - 20-TERMINAL



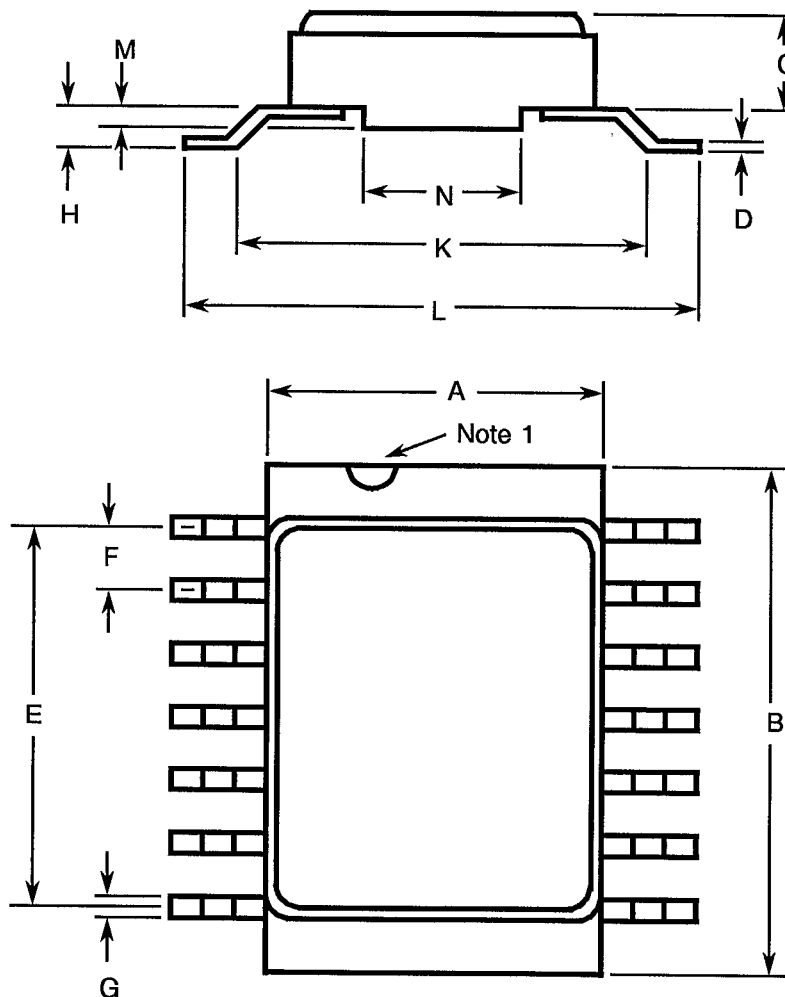
DIMENSIONS	MILLIMETRES		NOTES
	MIN	MAX	
A	1.14	1.95	
A1	1.63	2.36	
B	0.55	0.72	3
C	1.06	1.47	3
C ₁	1.91	2.41	
D	8.67	9.09	
D1	7.21	7.52	
d, d1	1.27	TYPICAL	4
d2	7.62	TYPICAL	
E	8.67	9.09	
E1	7.21	7.52	
e, e1	1.27	TYPICAL	4
e2	7.62	TYPICAL	
f, g	-	0.76	
h, h1	1.01	TYPICAL	6
j, j1	0.51	TYPICAL	5

NOTES: See Page 11.



FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(d) - SMALL OUTLINE CERAMIC PACKAGE, 14-PIN



SYMBOL	MILLIMETRES		NOTES
	MIN.	MAX.	
A	6.75	7.06	
B	9.76	10.14	
C	1.49	1.95	
D	0.102	0.152	3
E	7.50	7.75	
F	1.27 TYPICAL		4
G	0.38	0.48	3
H	0.60	0.90	3
K	9.00 TYPICAL		
L	10	10.65	
M	0.33	0.43	
N	4.31 TYPICAL		

NOTES: See Page 11.


 SCC	ESA/SCC Detail Specification No. 9201/061		PAGE 11 ISSUE 3
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FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

NOTES TO FIGURES 2(a) TO 2(d) INCLUSIVE

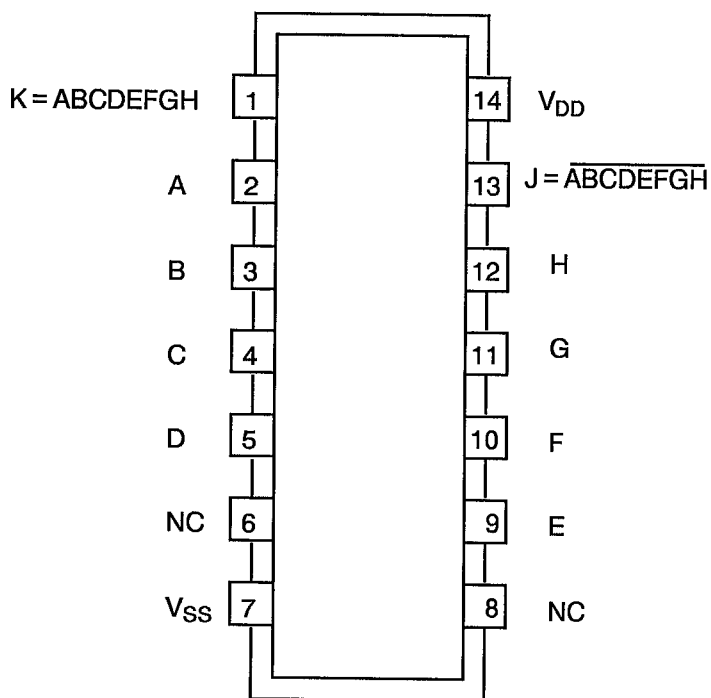
1. Index area: a notch, letter or dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages the index shall be as defined in Figure 2(c).
2. The dimension shall be measured from the seating plane to the base plane.
3. All leads or terminals.
4. Twelve spaces.
5. Index corner only.
6. Three non-index corners.
7. For all pins, either pin shape may be supplied.



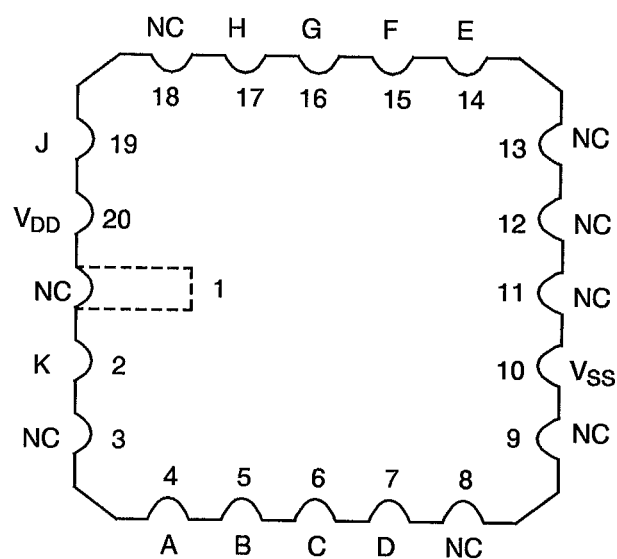
FIGURE 3(a) - PIN ASSIGNMENT

DUAL-IN-LINE, SO AND FLAT PACKAGES

CHIP CARRIER PACKAGE



TOP VIEW



TOP VIEW

FLAT PACKAGE, SO AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

FLAT PACKAGE, SO AND

DUAL-IN-LINE PIN OUTS 1 2 3 4 5 6 7 8 9 10 11 12 13 14

CHIP CARRIER PIN OUTS 2 4 5 6 7 9 10 12 14 15 16 17 19 20



FIGURE 3(b) - TRUTH TABLE

INPUTS								OUTPUTS	
A	B	C	D	E	F	G	H	J	K
L	L	L	L	L	L	L	L	H	L
H	L	L	L	L	L	L	L	H	L
L	H	L	L	L	L	L	L	H	L
L	L	H	L	L	L	L	L	H	L
L	L	L	H	L	L	L	L	H	L
L	L	L	L	H	L	L	L	H	L
L	L	L	L	L	H	L	L	H	L
L	L	L	L	L	L	H	L	H	L
L	L	L	L	L	L	L	H	H	L
.
.
H	H	H	H	H	H	H	L	H	L
H	H	H	H	H	H	H	H	L	H

NOTES

1. Logic Level Definitions: L= Low Level, H= High Level.
2. Positive Logic: $J = \overline{A.B.C.D.E.F.G.H}$, $K = A.B.C.D.E.F.G.H$



FIGURE 3(c) - CIRCUIT SCHEMATIC

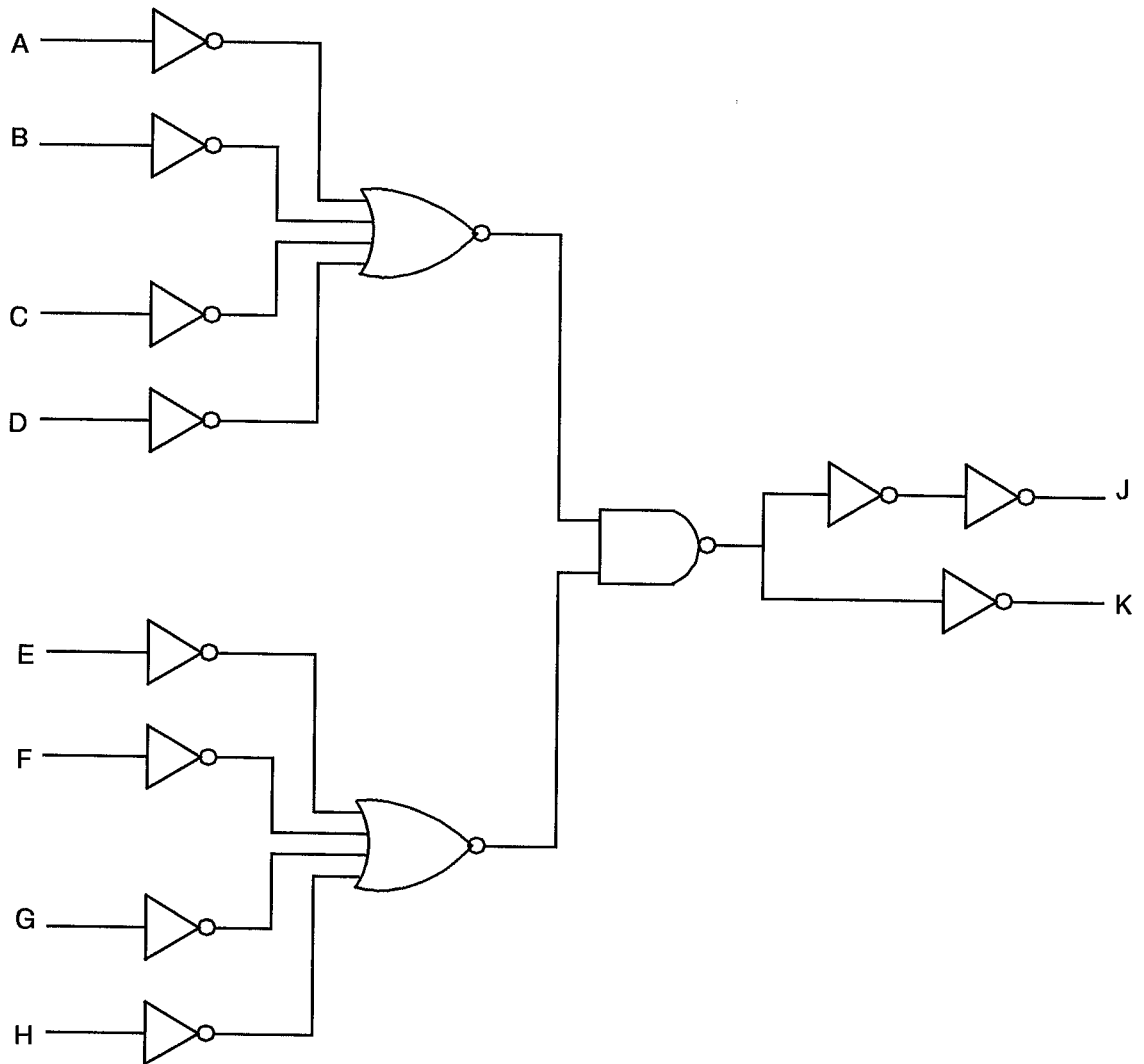


FIGURE 3(d) - FUNCTIONAL DIAGRAM

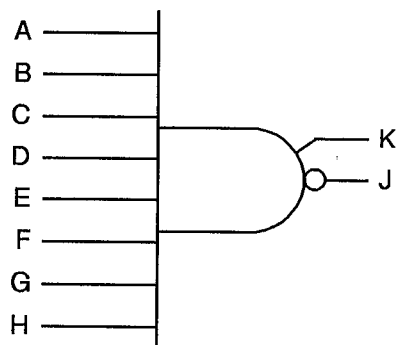
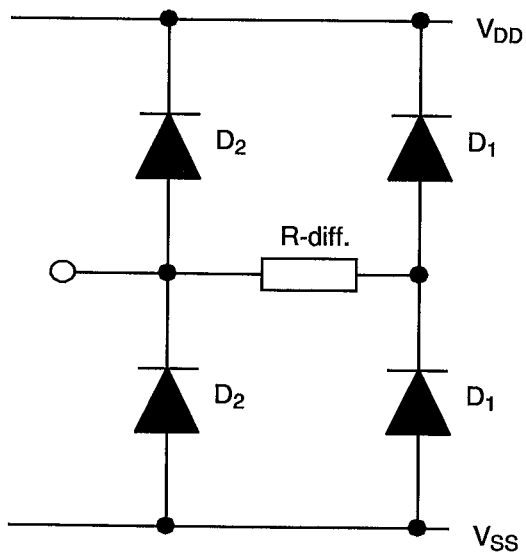


FIGURE 3(e) - INPUT PROTECTION NETWORK



**2. APPLICABLE DOCUMENTS**

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:

V_{IC} = Input Clamp Voltage
 P_{DSO} = Single Output Power Dissipation
CKT = Circuit.

4. REQUIREMENTS**4.1 GENERAL**

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION**4.2.1 Deviations from Special In-process Controls**

None.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in Tests (Chart III)**4.2.3.1 Deviations from High Temperature Reverse Bias (H.T.R.B.)**

Prior to operating power burn-in, a high temperature reverse bias (H.T.R.B.) screen at +125°C shall be added for the N-Channel and then for the P-Channel in accordance with Tables 5(a) and 5(b) of this specification. Each exposure to H.T.R.B. shall be 72 hours and Table 4 Parameter Drift Values shall be applied at 0 and 144 hours.



4.2.4 Deviations from Qualification Tests (Chart IV)

None.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 1.34 grammes for the dual-in-line package, 0.58 grammes for the flat and SO packages and 0.52 grammes for the chip carrier package.

4.4 MATERIALS AND FINISHES

The materials shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed or preform-soldered.

4.4.2 Lead Material and Finish

For dual-in-line and flat packages, the material shall be Type 'G' with either Type '4' or Type '2 or 8' finish in accordance with ESA/SCC Basic Specification No. 23500. For chip carrier packages the finish shall be Type '2' in accordance with ESA/SCC Basic Specification No. 23500. For SO ceramic packages, the material shall be Type 'G' with either Type '2' or Type '4' finish in accordance with ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

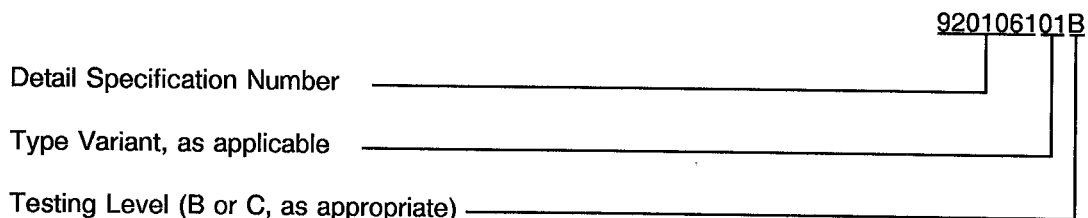
- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

For dual-in-line, flat and SO packages, an index shall be located at the top of the package-in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(c).

**4.5.3 The SCC Component Number**

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

**4.5.4 Traceability Information**

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS**4.6.1 Electrical Measurements at Room Temperature**

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at $T_{amb} = +125(+0-5)$ °C and $-55(+5-0)$ °C respectively.

4.6.3 Circuits for Electrical Measurements

Circuits and functional test sequence for use in performing electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS**4.7.1 Parameter Drift Values**

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $+22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for H.T.R.B. and Burn-in

The requirements for H.T.R.B. and Burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for H.T.R.B. and Burn-in shall be as specified in Tables 5(a), 5(b) and 5(c) of this specification.

4.7.3 Electrical Circuits for H.T.R.B and Burn-in

Circuits for use in performing the H.T.R.B. and Burn-in tests are shown in Figures 5(a), 5(b) and 5(c) of this specification.

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
1	Functional Test	-	-	4(a)	Verify Truth Table without Load. $V_{DD} = 3V_{dc}$, $V_{SS} = 0V_{dc}$ Notes 1 and 2	-	-	-
2	Functional Test	-	-	4(a)	Verify Truth Table without Load. $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Notes 1 and 2	-	-	-
3 to 4	Quiescent Current	I_{DD}	3005	4(b)	$V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 14) (Pin C 20)	-	100	nA
5 to 12	Input Current Low Level	I_{IL}	3009	4(c)	V_{IN} (Under Test) = $0V_{dc}$ V_{IN} (Remaining Inputs) = $15V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	-50	nA
13 to 20	Input Current High Level	I_{IH}	3010	4(d)	V_{IN} (Under Test) = $15V_{dc}$ V_{IN} (Remaining Inputs) = $0V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	50	nA
21	Output Voltage Low Level NAND Output	V_{OL}	3007	4(e)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	0.05	V
22 to 29	Output Voltage Low Level AND Output	V_{OL}	3007	4(f)	Input Conditions as per Table 4(f) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	0.05	V

NOTES: See Page 25.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
30 to 37	Output Voltage High Level NAND Output	V_{OH}	3006	4(f)	Input Conditions as per Table 4(f) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	14.95	-	V
38	Output Voltage High Level AND Output	V_{OH}	3006	4(e)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	14.95	-	V
39	Output Drive Current N-Channel NAND Output	I_{OL1}	-	4(g)	All Inputs: $V_{IN} = 5V_{dc}$ $V_{OUT} = 0.4V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	0.51	-	mA
40 to 47	Output Drive Current N-Channel AND Output	I_{OL1}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $V_{OUT} = 0.4V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	0.51	-	mA
48	Output Drive Current N-Channel NAND Output	I_{OL2}	-	4(g)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = 1.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	3.4	-	mA
49 to 56	Output Drive Current N-Channel AND Output	I_{OL2}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = 1.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	3.4	-	mA

NOTES: See Page 25.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
57 to 64	Output Drive Current P-Channel NAND Output	I_{OH1}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $V_{OUT} = 4.6V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	-0.51	-	mA
65	Output Drive Current P-Channel AND Output	I_{OH1}	-	4(g)	All Inputs: $V_{IN} = 5V_{dc}$ $V_{OUT} = 4.6V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	-0.51	-	mA
66 to 73	Output Drive Current P-Channel NAND Output	I_{OH2}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = 13.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	-3.4	-	mA
74	Output Drive Current P-Channel AND Output	I_{OH2}	-	4(g)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = 13.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	-3.4	-	mA
75 to 82	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL1}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 1.5V_{dc}$, $V_{IH} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	4.5	-	V
83 to 90	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL1}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 1.5V_{dc}$, $V_{IH} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	0.5	V

NOTES: See Page 25.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
91 to 98	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL2}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	13.5	-	V
99 to 106	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL2}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	1.5	V
107	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH1}	-	4(j)	All Inputs: $V_{IN} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	0.5	V
108	Input Voltage High Level (Noise Immunity) AND Output	V_{IH1}	-	4(j)	All Inputs: $V_{IN} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	4.5	-	V
109	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH2}	-	4(j)	All Inputs: $V_{IN} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	1.5	V
110	Input Voltage High Level (Noise Immunity) AND Output	V_{IH2}	-	4(j)	All Inputs: $V_{IN} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	13.5	-	V
111	Threshold Voltage N-Channel	V_{THN}	-	4(k)	A Input at Ground All Other Inputs: $V_{IN} = 5V_{dc}$ $V_{DD} = 5V_{dc}$, $I_{SS} = -10\mu A$ (Pin D/F 7) (Pin C 10)	-0.7	-3.0	V
112	Threshold Voltage P-Channel	V_{THP}	-	4(l)	A Input at Ground All Other Inputs: $V_{IN} = -5V_{dc}$ $V_{SS} = -5V_{dc}$, $I_{DD} = 10\mu A$ (Pin D/F 14) (Pin C 20)	0.7	3.0	V

NOTES: See Page 25.



SEC

ESA/SCC Detail Specification
No. 9201/061

PAGE 23

ISSUE 3

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
113 to 120	Input Clamp Voltage (to V_{SS})	V_{IC1}	-	4(m)	I_{IN} (Under Test) = $-100\mu A$ V_{DD} = Open, V_{SS} = 0Vdc All Other Pins Open (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	-2.0	V
121 to 128	Input Clamp Voltage (to V_{DD})	V_{IC2}	-	4(n)	V_{IN} (Under Test) = 6Vdc V_{SS} = Open, $R = 30k\Omega$; (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	3.0	-	V

NOTES: See Page 25.

**TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
129 to 136	Input Capacitance	C_{IN}	3012	4(o)	V_{IN} (Not Under Test) = 0Vdc $V_{DD} = V_{SS} = 0Vdc$ Note 4 (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	7.5	pF
137	Propagation Delay Low to High	t_{PLH}	3003	4(p)	V_{IN} (Under Test) = Pulse Generator V_{IN} (All Other Inputs) = 5Vdc $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 5 <u>Pins D/F</u> <u>Pins C</u> 2 to 13 4 to 19	-	250	ns
138	Propagation Delay High to Low	t_{PHL}	3003	4(p)	V_{IN} (Under Test) = Pulse Generator V_{IN} (All Other Inputs) = 5Vdc $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 5 <u>Pins D/F</u> <u>Pins C</u> 2 to 13 4 to 19	-	250	ns
139	Transition Time Low to High	t_{TLH}	3004	4(p)	V_{IN} (Under Test) = Pulse Generator V_{IN} (All Other Inputs) = 0Vdc $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 5 (Pin D/F 13) (Pin C 19)	-	150	ns
140	Transition Time High to Low	t_{THL}	3004	4(p)	V_{IN} (Under Test) = Pulse Generator V_{IN} (All Other Inputs) = 0Vdc $V_{DD} = 5Vdc, V_{SS} = 0Vdc$ Note 5 (Pin D/F 13) (Pin C 19)	-	150	ns

NOTES: See Page 25.

**SCC**

ESA/SCC Detail Specification

No. 9201/061

PAGE 25

ISSUE 3

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE (CONT'D)**NOTES**

1. GO-NO-GO Test, each pattern of Test Table 4(a).
 $V_{OH} \geq V_{DD} - 0.5V_{dc}$ $V_{OL} \leq 0.5V_{dc}$
2. Maximum time to output comparator strobe 300 μ sec.
3. Interchange of forcing and measuring function is permitted.
4. Measurement performed on a sample basis LTPD 7, or less, with a Capacitance Bridge connected between each input under test and V_{SS} , only for Lots where LAT Level 2 is to be performed. (For LTPD sampling plan, see Annexe I of ESA/SCC 9000).
5. Measurement performed on a sample basis LTPD 7, or less (see Annexe I of ESA/SCC 9000).



TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, + 125(+0 – 5) °C

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
1	Functional Test	-	-	4(a)	Verify Truth Table without Load. $V_{DD} = 3V_{dc}$, $V_{SS} = 0V_{dc}$ Notes 1 and 2	-	-	-
2	Functional Test	-	-	4(a)	Verify Truth Table without Load. $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Notes 1 and 2	-	-	-
3 to 4	Quiescent Current	I_{DD}	3005	4(b)	$V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 14) (Pin C 20)	-	1.0	μA
5 to 12	Input Current Low Level	I_{IL}	3009	4(c)	V_{IN} (Under Test) = $0V_{dc}$ V_{IN} (Remaining Inputs) = $15V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	-100	nA
13 to 20	Input Current High Level	I_{IH}	3010	4(d)	V_{IN} (Under Test) = $15V_{dc}$ V_{IN} (Remaining Inputs) = $0V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	100	nA
21	Output Voltage Low Level NAND Output	V_{OL}	3007	4(e)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	0.05	V
22 to 29	Output Voltage Low Level AND Output	V_{OL}	3007	4(f)	Input Conditions as per Table 4(f) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	0.05	V

NOTES: See Page 25.

**TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, +125(+0 - 5) °C (CONT'D)**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
30 to 37	Output Voltage High Level NAND Output	V_{OH}	3006	4(f)	Input Conditions as per Table 4(f) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	14.95	-	V
38	Output Voltage High Level AND Output	V_{OH}	3006	4(e)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	14.95	-	V
39	Output Drive Current N-Channel NAND Output	I_{OL1}	-	4(g)	All Inputs: $V_{IN} = 5V_{dc}$ $V_{OUT} = 0.4V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	0.36	-	mA
40 to 47	Output Drive Current N-Channel AND Output	I_{OL1}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $V_{OUT} = 0.4V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	0.36	-	mA
48	Output Drive Current N-Channel NAND Output	I_{OL2}	-	4(g)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = 1.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	2.4	-	mA
49 to 56	Output Drive Current N-Channel AND Output	I_{OL2}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = 1.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	2.4	-	mA

NOTES: See Page 25.



TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, +125(+0-5) °C (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
57 to 64	Output Drive Current P-Channel NAND Output	I_{OH1}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $V_{OUT} = 4.6V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	-0.36	-	mA
65	Output Drive Current P-Channel AND Output	I_{OH1}	-	4(g)	All Inputs: $V_{IN} = 5V_{dc}$ $V_{OUT} = 4.6V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	-0.36	-	mA
66 to 73	Output Drive Current P-Channel NAND Output	I_{OH2}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = 13.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	-2.4	-	mA
74	Output Drive Current P-Channel AND Output	I_{OH2}	-	4(g)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = 13.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	-2.4	-	mA
75 to 82	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL1}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 1.5V_{dc}$, $V_{IH} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	4.5	-	V
83 to 90	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL1}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 1.5V_{dc}$, $V_{IH} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	0.5	V

NOTES: See Page 25.

**TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, +125(+0-5) °C (CONT'D)**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
91 to 98	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL2}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	13.5	-	V
99 to 106	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL2}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	1.5	V
107	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH1}	-	4(j)	All Inputs: $V_{IN} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	0.5	V
108	Input Voltage High Level (Noise Immunity) AND Output	V_{IH1}	-	4(j)	All Inputs: $V_{IN} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	4.5	-	V
109	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH2}	-	4(j)	All Inputs: $V_{IN} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	1.5	V
110	Input Voltage High Level (Noise Immunity) AND Output	V_{IH2}	-	4(j)	All Inputs: $V_{IN} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	13.5	-	V
111	Threshold Voltage N-Channel	V_{THN}	-	4(k)	A Input at Ground All Other Inputs: $V_{IN} = 5V_{dc}$ $V_{DD} = 5V_{dc}$, $I_{SS} = -10\mu A$ (Pin D/F 7) (Pin C 10)	-0.3	-3.5	V
112	Threshold Voltage P-Channel	V_{THP}	-	4(l)	A Input at Ground All Other Inputs: $V_{IN} = -5V_{dc}$ $V_{SS} = -5V_{dc}$, $I_{DD} = 10\mu A$ (Pin D/F 14) (Pin C 20)	0.3	3.5	V

NOTES: See Page 25.

**TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, $-55(+5-0)^\circ\text{C}$**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
1	Functional Test	-	-	4(a)	Verify Truth Table without Load. $V_{DD} = 3\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ Notes 1 and 2	-	-	-
2	Functional Test	-	-	4(a)	Verify Truth Table without Load. $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ Notes 1 and 2	-	-	-
3 to 4	Quiescent Current	I_{DD}	3005	4(b)	$V_{IL} = 0\text{Vdc}$, $V_{IH} = 15\text{Vdc}$ $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pin D/F 14) (Pin C 20)	-	100	nA
5 to 12	Input Current Low Level	I_{IL}	3009	4(c)	V_{IN} (Under Test) = 0Vdc V_{IN} (Remaining Inputs) = 15Vdc $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	-50	nA
13 to 20	Input Current High Level	I_{IH}	3010	4(d)	V_{IN} (Under Test) = 15Vdc V_{IN} (Remaining Inputs) = 0Vdc $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	-	50	nA
21	Output Voltage Low Level NAND Output	V_{OL}	3007	4(e)	All Inputs: $V_{IN} = 15\text{Vdc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pin D/F 13) (Pin C 19)	-	0.05	V
22 to 29	Output Voltage Low Level AND Output	V_{OL}	3007	4(f)	Input Conditions as per Table 4(f) $V_{IL} = 0\text{Vdc}$, $V_{IH} = 15\text{Vdc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pin D/F 1) (Pin C 2)	-	0.05	V

NOTES: See Page 25.

**TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, -55(+5-0) °C (CONT'D)**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
30 to 37	Output Voltage High Level NAND Output	V_{OH}	3006	4(f)	Input Conditions as per Table 4(f) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	14.95	-	V
38	Output Voltage High Level AND Output	V_{OH}	3006	4(e)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = \text{Open}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	14.95	-	V
39	Output Drive Current N-Channel NAND Output	I_{OL1}	-	4(g)	All Inputs: $V_{IN} = 5V_{dc}$ $V_{OUT} = 0.4V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	0.64	-	mA
40 to 47	Output Drive Current N-Channel AND Output	I_{OL1}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 5V_{dc}$ $V_{OUT} = 0.4V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	0.64	-	mA
48	Output Drive Current N-Channel NAND Output	I_{OL2}	-	4(g)	All Inputs: $V_{IN} = 15V_{dc}$ $V_{OUT} = 1.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 13) (Pin C 19)	4.2	-	mA
49 to 56	Output Drive Current N-Channel AND Output	I_{OL2}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0V_{dc}$, $V_{IH} = 15V_{dc}$ $V_{OUT} = 1.5V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ Note 3 (Pin D/F 1) (Pin C 2)	4.2	-	mA

NOTES: See Page 25.



TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, $-55(+5-0)^\circ\text{C}$ (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
57 to 64	Output Drive Current P-Channel NAND Output	I_{OH1}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0\text{Vdc}$, $V_{IH} = 5\text{Vdc}$ $V_{OUT} = 4.6\text{Vdc}$ $V_{DD} = 5\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ Note 3 (Pin D/F 13) (Pin C 19)	-0.64	-	mA
65	Output Drive Current P-Channel AND Output	I_{OH1}	-	4(g)	All Inputs: $V_{IN} = 5\text{Vdc}$ $V_{OUT} = 4.6\text{Vdc}$ $V_{DD} = 5\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ Note 3 (Pin D/F 1) (Pin C 2)	-0.64	-	mA
66 to 73	Output Drive Current P-Channel NAND Output	I_{OH2}	-	4(h)	Input Conditions as per Table 4(h) $V_{IL} = 0\text{Vdc}$, $V_{IH} = 15\text{Vdc}$ $V_{OUT} = 13.5\text{Vdc}$ $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ Note 3 (Pin D/F 13) (Pin C 19)	-4.2	-	mA
74	Output Drive Current P-Channel AND Output	I_{OH2}	-	4(g)	All Inputs: $V_{IN} = 15\text{Vdc}$ $V_{OUT} = 13.5\text{Vdc}$ $V_{DD} = 15\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ Note 3 (Pin D/F 1) (Pin C 2)	-4.2	-	mA
75 to 82	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL1}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 1.5\text{Vdc}$, $V_{IH} = 3.5\text{Vdc}$ $V_{DD} = 5\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pin D/F 1) (Pin C 2)	4.5	-	V
83 to 90	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL1}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 1.5\text{Vdc}$, $V_{IH} = 3.5\text{Vdc}$ $V_{DD} = 5\text{Vdc}$, $V_{SS} = 0\text{Vdc}$ (Pin D/F 13) (Pin C 19)	-	0.5	V

NOTES: See Page 25.

**TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, $-55(+5-0)$ °C (CONT'D)**

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
91 to 98	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL2}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	13.5	-	V
99 to 106	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL2}	-	4(i)	Input Conditions as per Table 4(i) $V_{IL} = 4V_{dc}$, $V_{IH} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	-	1.5	V
107	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH1}	-	4(j)	All Inputs: $V_{IN} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	0.5	V
108	Input Voltage High Level (Noise Immunity) AND Output	V_{IH1}	-	4(j)	All Inputs: $V_{IN} = 3.5V_{dc}$ $V_{DD} = 5V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	4.5	-	V
109	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH2}	-	4(j)	All Inputs: $V_{IN} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 1) (Pin C 2)	-	1.5	V
110	Input Voltage High Level (Noise Immunity) AND Output	V_{IH2}	-	4(j)	All Inputs: $V_{IN} = 11V_{dc}$ $V_{DD} = 15V_{dc}$, $V_{SS} = 0V_{dc}$ (Pin D/F 13) (Pin C 19)	13.5	-	V
111	Threshold Voltage N-Channel	V_{THN}	-	4(k)	A Input at Ground All Other Inputs: $V_{IN} = 5V_{dc}$ $V_{DD} = 5V_{dc}$, $I_{SS} = -10\mu A$ (Pin D/F 7) (Pin C 10)	-0.7	-3.5	V
112	Threshold Voltage P-Channel	V_{THP}	-	4(l)	A Input at Ground All Other Inputs: $V_{IN} = -5V_{dc}$ $V_{SS} = -5V_{dc}$, $I_{DD} = 10\mu A$ (Pin D/F 14) (Pin C 20)	0.7	3.5	V

NOTES: See Page 25.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4 (a) - FUNCTIONAL TEST TABLE

PATTERN NO.	PIN NUMBERS												D.C. SUPPLY	
	1	2	3	4	5	6	8	9	10	11	12	13	7	14
1	0	0	0	0	0	0	0	0	0	0	0	1	0	V _{DD}
2	1	1	1	1	1	0	0	1	1	1	1	0	↓	↓
3	0	1	1	1	1	0	0	1	1	1	0	1		
4	1	1	1	1	1	0	0	1	1	1	1	0		
5	0	1	1	1	1	0	0	1	1	0	1	1		
6	1	1	1	1	1	0	0	1	1	1	1	0		
7	0	1	1	1	1	0	0	1	0	1	1	1		
8	1	1	1	1	1	0	0	1	1	1	1	0		
9	0	1	1	1	1	0	0	0	1	1	1	1		
10	1	1	1	1	1	0	0	1	1	1	1	0		
11	0	1	1	1	0	0	0	1	1	1	1	1		
12	1	1	1	1	1	0	0	1	1	1	1	0		
13	0	1	1	0	1	0	0	1	1	1	1	1		
14	1	1	1	1	1	0	0	1	1	1	1	0		
15	0	1	0	1	1	0	0	1	1	1	1	1		
16	1	1	1	1	1	0	0	1	1	1	1	0		
17	0	0	1	1	1	0	0	1	1	1	1	1		
18	1	1	1	1	1	0	0	1	1	1	1	0		

NOTES

- Figure 4(a) illustrates one series of Test Patterns. Any other pattern series must be agreed with the Qualifying Space Agency and shall be included as an Appendix.
- Logic Level Definitions: 1 = V_{IH} = V_{DD}, 0 = V_{IL} = V_{SS}.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(b) - QUIESCENT CURRENT

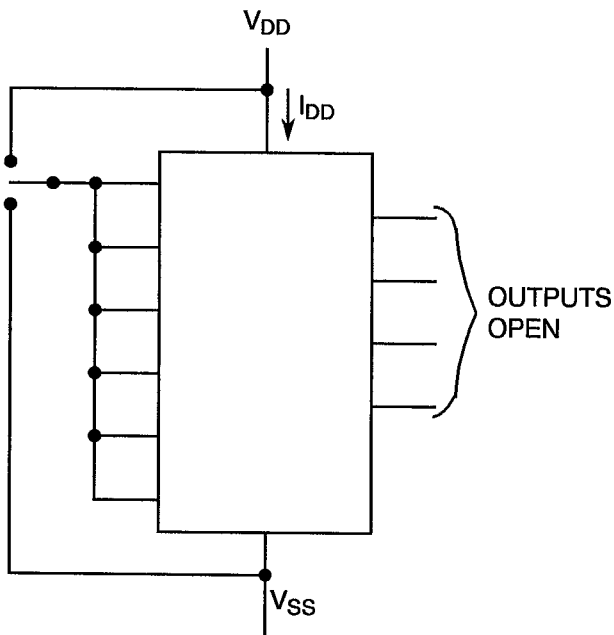
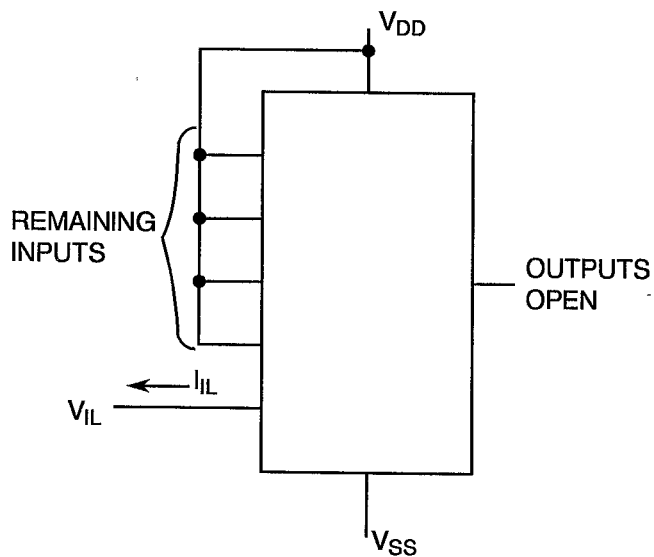


FIGURE 4(c) - INPUT CURRENT LOW LEVEL



NOTES

1. Each input to be tested separately.

FIGURE 4(d) - INPUT CURRENT HIGH LEVEL

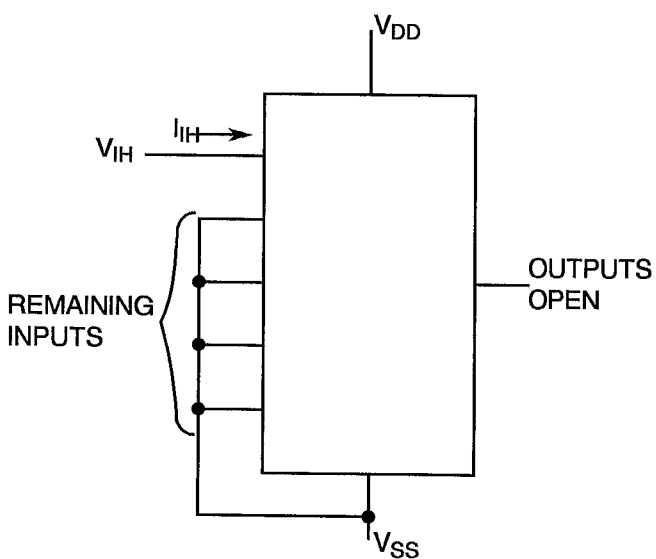
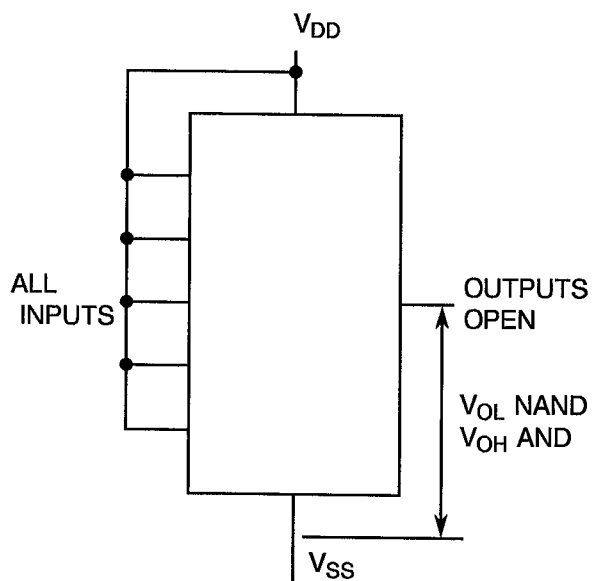


FIGURE 4(e) - OUTPUT VOLTAGE LOW LEVEL FOR NAND OUTPUT AND OUTPUT VOLTAGE HIGH LEVEL FOR AND OUTPUT



NOTES

1. Each input to be tested separately.

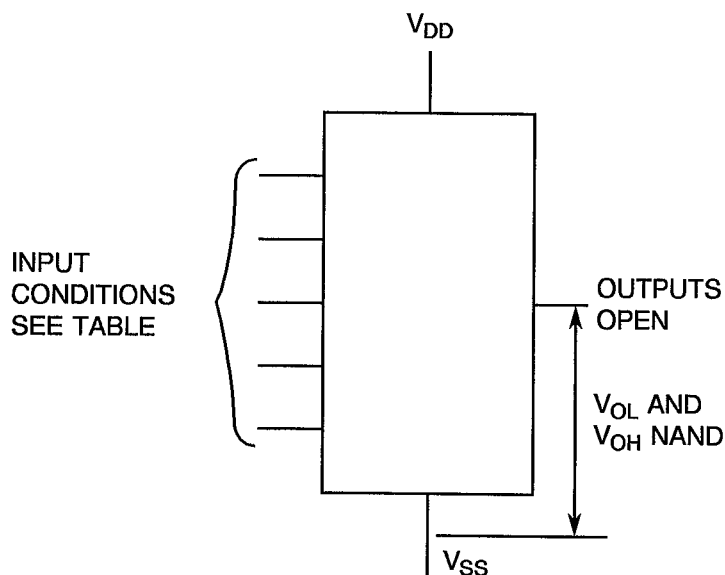
NOTES

1. Each output to be tested separately.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(f) - OUTPUT VOLTAGE LOW LEVEL FOR AND OUTPUT AND OUTPUT VOLTAGE HIGH LEVEL FOR NAND OUTPUT

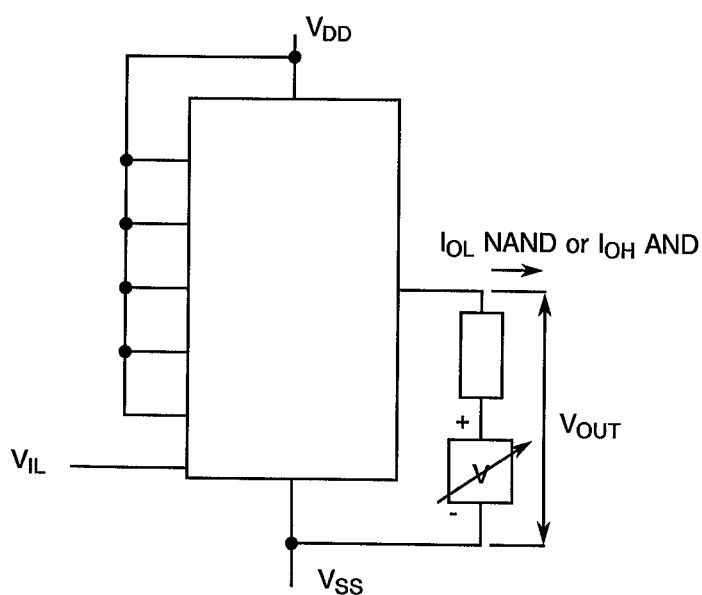


TEST NO.	INPUT CONDITIONS (PIN NUMBERS)							
	2	3	4	5	9	10	11	12
1	0	1	1	1	1	1	1	1
2	1	0	1	1	1	1	1	1
3	1	1	0	1	1	1	1	1
4	1	1	1	0	1	1	1	1
5	1	1	1	1	0	1	1	1
6	1	1	1	1	1	0	1	1
7	1	1	1	1	1	1	0	1
8	1	1	1	1	1	1	1	0

NOTES

1. Logic Level Definitions: 1 = $V_{IH} = V_{DD}$, 0 = $V_{IL} = V_{SS}$.
2. Each output to be tested separately.

FIGURE 4(g) - LOW LEVEL OUTPUT CURRENT FOR NAND OUTPUT AND HIGH LEVEL OUTPUT CURRENT FOR AND OUTPUT



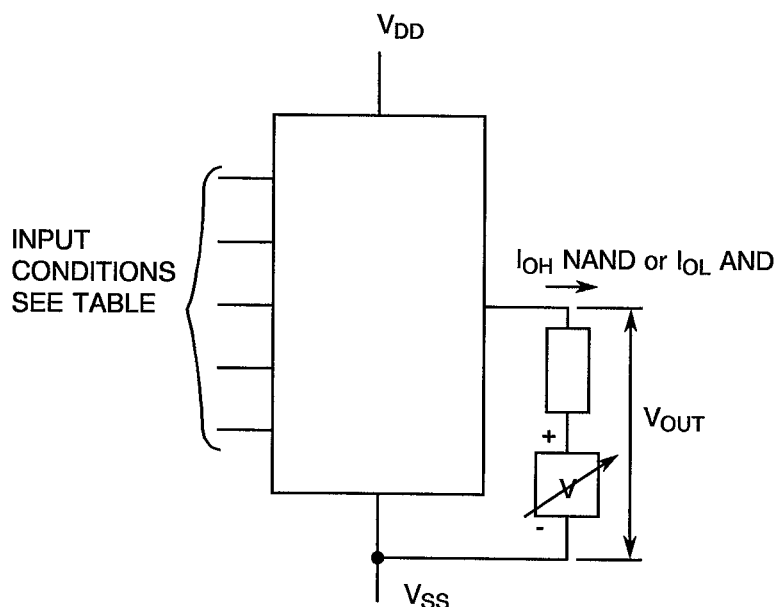
NOTES

1. Each output to be tested separately.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(h) - HIGH LEVEL OUTPUT CURRENT FOR NAND OUTPUT AND LOW LEVEL OUTPUT CURRENT FOR AND OUTPUT

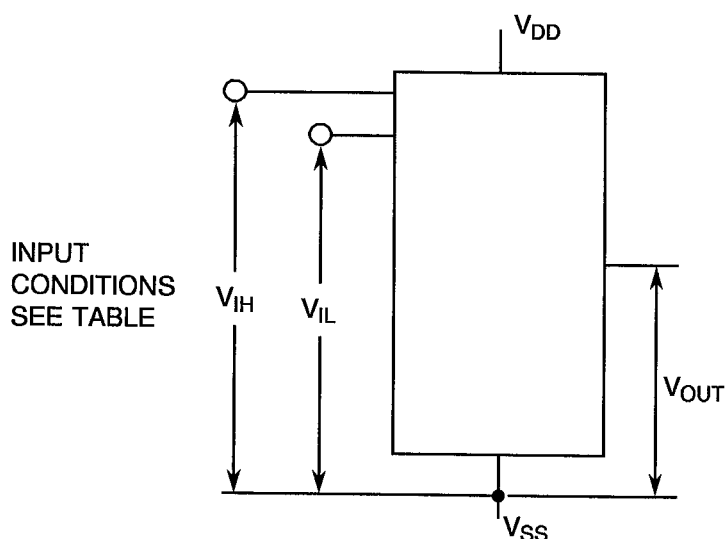


TEST NO.	INPUT CONDITIONS (PIN NUMBERS)							
	2	3	4	5	9	10	11	12
1	0	0	0	0	0	0	0	0
2	1	0	0	0	0	0	0	0
3	1	1	0	0	0	0	0	0
4	1	1	1	0	0	0	0	0
5	1	1	1	1	0	0	0	0
6	1	1	1	1	1	0	0	0
7	1	1	1	1	1	1	0	0
8	1	1	1	1	1	1	1	0

NOTES

1. Logic Level Definitions: 1 = $V_{IH} = V_{DD}$, 0 = $V_{IL} = V_{SS}$.
2. Each output to be tested separately.

FIGURE 4(i) - LOW LEVEL INPUT VOLTAGE



TEST NO.	INPUT CONDITIONS (PIN NUMBERS)							
	2	3	4	5	9	10	11	12
1	0	1	1	1	1	1	1	1
2	1	0	1	1	1	1	1	1
3	1	1	0	1	1	1	1	1
4	1	1	1	0	1	1	1	1
5	1	1	1	1	0	1	1	1
6	1	1	1	1	1	0	1	1
7	1	1	1	1	1	1	0	1
8	1	1	1	1	1	1	1	0

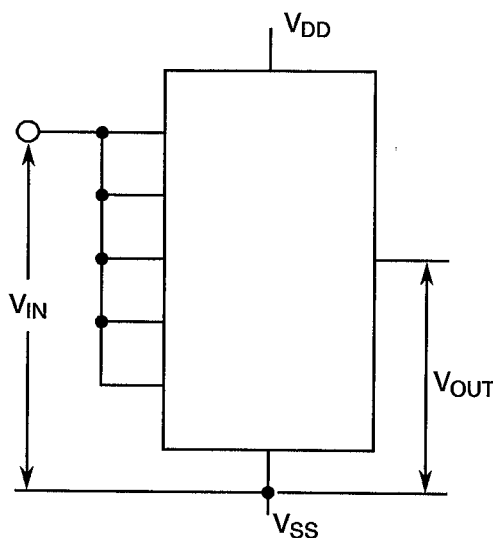
NOTES

1. Logic Level Definitions: 1 = $V_{IH} = V_{DD}$, 0 = $V_{IL} = V_{SS}$.
2. Each output to be tested separately.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(j) - HIGH LEVEL INPUT VOLTAGE



NOTES

- 1. Each output to be tested separately.

FIGURE 4(k) - THRESHOLD VOLTAGE N-CHANNEL

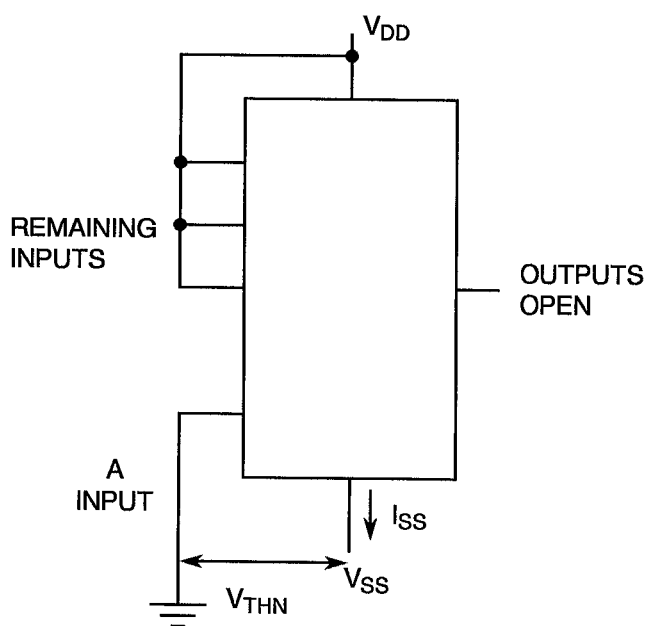


FIGURE 4(l) - THRESHOLD VOLTAGE P-CHANNEL

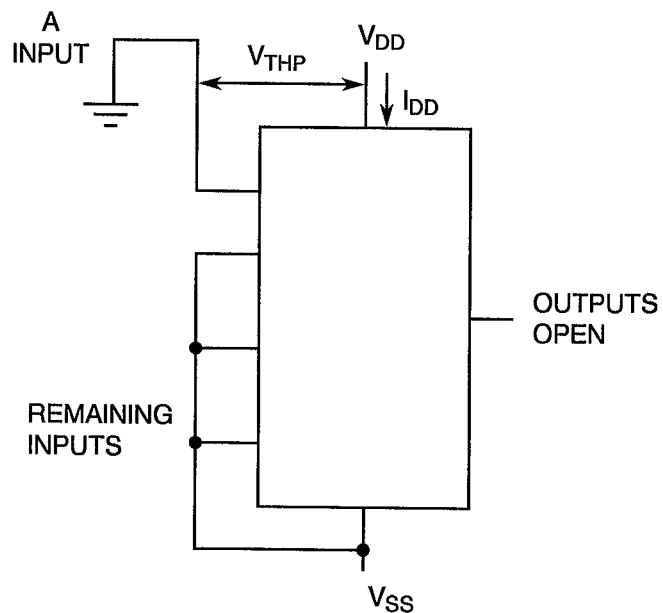
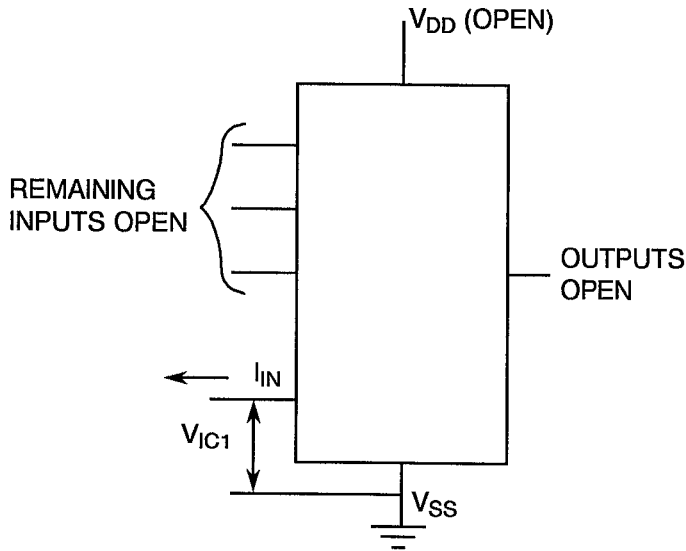




FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

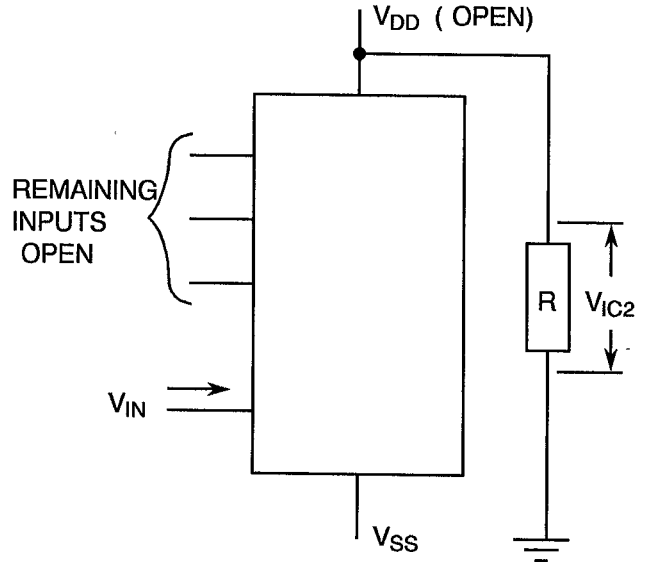
FIGURE 4(m) - INPUT CLAMP VOLTAGE (TO V_{SS})



NOTES

1. Each input to be tested separately.

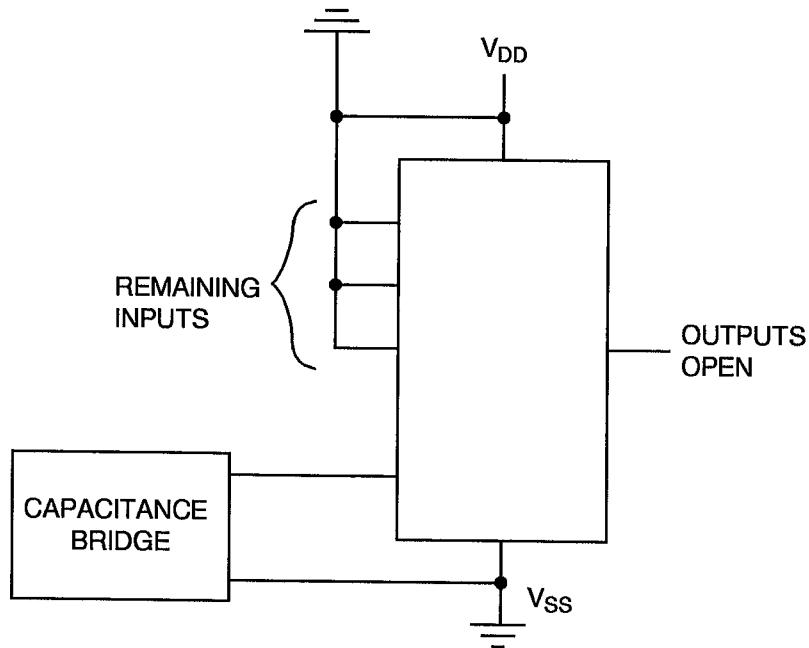
FIGURE 4(n) - INPUT CLAMP VOLTAGE (TO V_{DD})



NOTES

1. Each input to be tested separately.

FIGURE 4(o) - INPUT CAPACITANCE



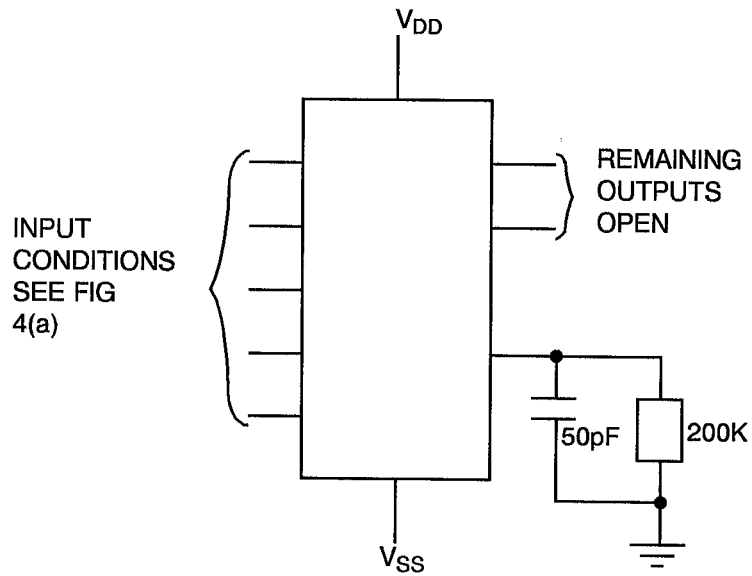
NOTES

1. Each input to be tested separately.
2. $f = 100\text{kHz to }1\text{MHz}$.

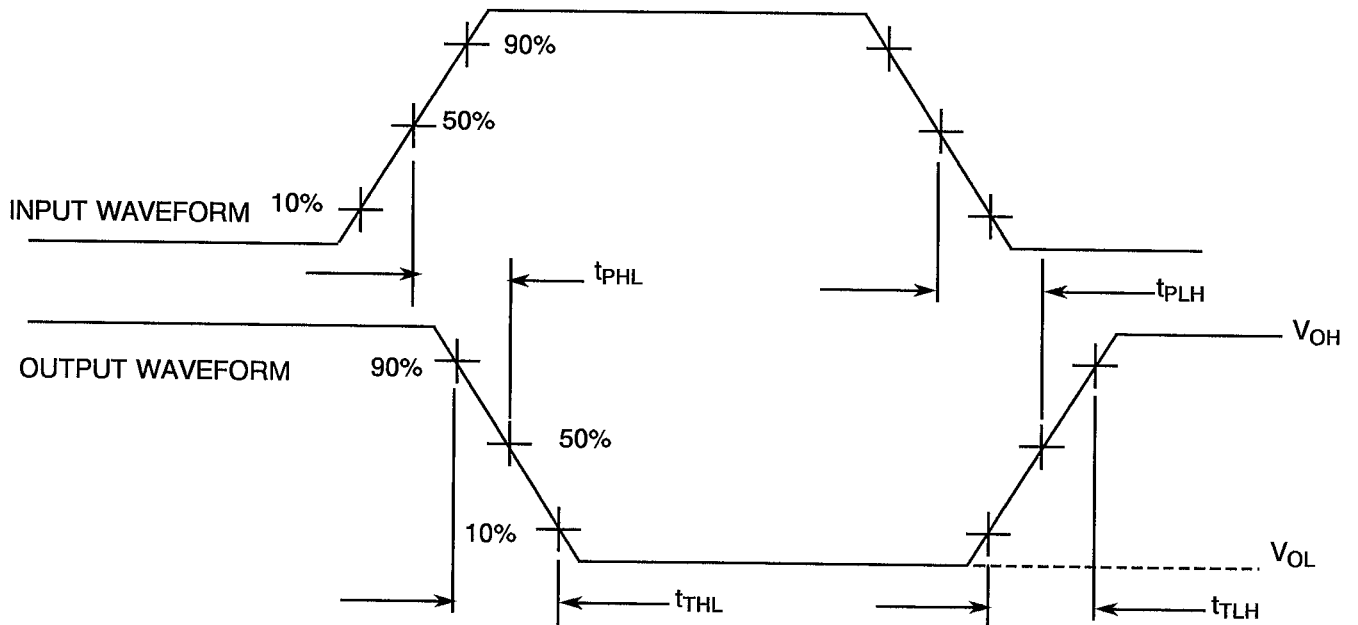


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(p) - PROPAGATION DELAY AND TRANSITION TIME



VOLTAGE WAVEFORMS



NOTES

1. Pulse Generator - $V_P = 0$ to V_{DD} , t_r and $t_f \leq 15\text{ns}$, $f = 500\text{kHz}$.

**TABLE 4 - PARAMETER DRIFT VALUES**

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
3 to 4	Quiescent Current	I_{DD}	As per Table 2	As per Table 2	± 50	nA
39	Output Drive Current N-Channel NAND Output	I_{OL1}	As per Table 2	As per Table 2	± 15 (1)	%
40 to 47	Output Drive Current N-Channel AND Output	I_{OL1}	As per Table 2	As per Table 2	± 15 (1)	%
57 to 64	Output Drive Current P-Channel NAND Output	I_{OH1}	As per Table 2	As per Table 2	± 15 (1)	%
65	Output Drive Current P-Channel AND Output	I_{OH1}	As per Table 2	As per Table 2	± 15 (1)	%
111	Threshold Voltage N-Channel	V_{THN}	As per Table 2	As per Table 2	± 0.3	V
112	Threshold Voltage P-Channel	V_{THP}	As per Table 2	As per Table 2	± 0.3	V

NOTES

1. Percentage of limit value if voltage is the measurement function.

**TABLE 5(a) - CONDITIONS FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, N-CHANNELS**

NO.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T_{amb}	+ 125(+ 0-5)	°C
2	Outputs - (Pins D/F 1-13) (Pins C 2-19)	V_{OUT}	Open	-
3	Inputs - (Pins D/F 9-10-11-12) (Pins C 14-15-16-17)	V_{IN}	V_{DD}	Vdc
4	Inputs - (Pins D/F 2-3-4-5) (Pins C 4-5-6-7)	V_{IN}	Ground	Vdc
5	Positive Supply Voltage (Pin D/F 14) (Pin C 20)	V_{DD}	15	Vdc
6	Negative Supply Voltage (Pin D/F 7) (Pin C 10)	V_{SS}	Ground	Vdc

NOTES

1. Input Load = Protection Resistor = 2k Ω minimum to 47k Ω maximum.

TABLE 5(b) - CONDITIONS FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, P-CHANNELS

NO.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T_{amb}	+ 125(+ 0-5)	°C
2	Outputs - (Pins D/F 1-13) (Pins C 2-19)	V_{OUT}	Open	-
3	Inputs - (Pins D/F 9-10-11-12) (Pins C 14-15-16-17)	V_{IN}	Ground	Vdc
4	Inputs - (Pins D/F 2-3-4-5) (Pins C 4-5-6-7)	V_{IN}	V_{DD}	Vdc
5	Positive Supply Voltage (Pin D/F 14) (Pin C 20)	V_{DD}	15	Vdc
6	Negative Supply Voltage (Pin D/F 7) (Pin C 10)	V_{SS}	Ground	Vdc

NOTES

1. Input Load = Protection Resistor = 2k Ω minimum to 47k Ω maximum.



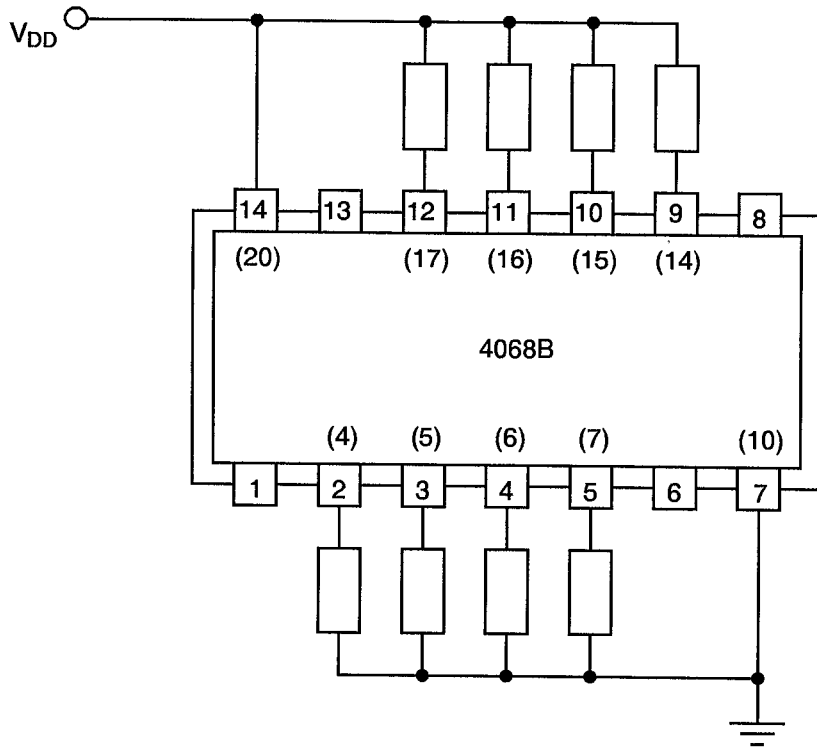
TABLE 5(c) - CONDITIONS FOR BURN-IN DYNAMIC

NO.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T_{amb}	+ 125(+ 0-5)	°C
2	Outputs - (Pins D/F 1-13) (Pins C 2-19)	V_{OUT}	$V_{DD}/2$	Vdc
3	Input - (Pins D/F 2-3-4-5-9-10-11-12) (Pins C 4-5-6-7-14-15-16-17)	V_{IN}	V_{GEN}	Vac
4	Pulse Voltage	V_{GEN}	0 to V_{DD}	Vac
5	Pulse Frequency Square Wave	f	$50k \leq f < 1M$ 50% Duty Cycle	Hz
6	Positive Supply Voltage (Pin D/F 14) (Pin C 20)	V_{DD}	15	Vdc
7	Negative Supply Voltage (Pin D/F 7) (Pin C 10)	V_{SS}	Ground	Vdc

NOTES 1. Input Load = Output Load = 2k Ω minimum to 47k Ω maximum.



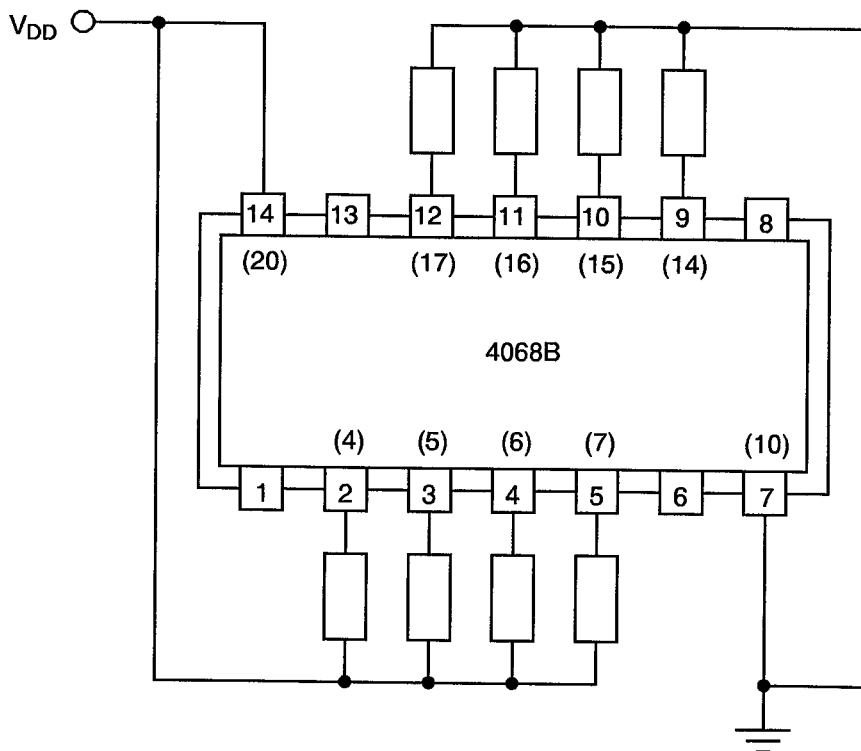
FIGURE 5(a) - ELECTRICAL CIRCUIT FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, N-CHANNELS



NOTES

1. Pin numbers in parenthesis are for the chip carrier package.

FIGURE 5(b) - ELECTRICAL CIRCUIT FOR BURN-IN HIGH TEMPERATURE REVERSE BIAS, P-CHANNELS

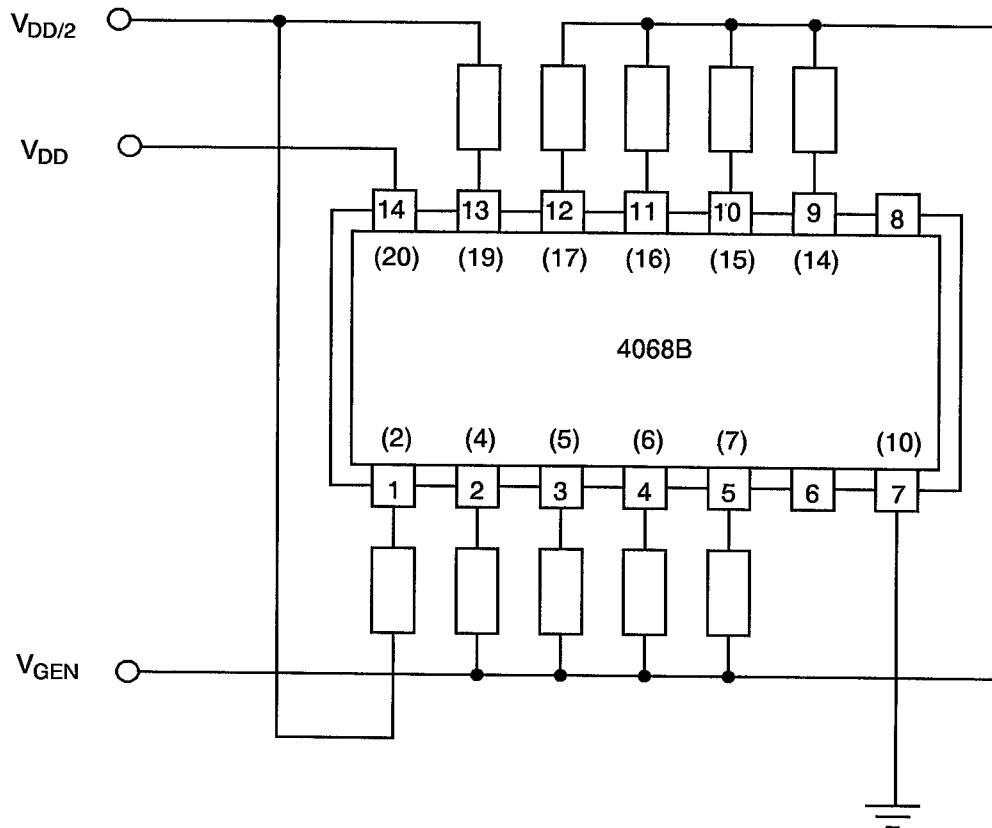


NOTES

1. Pin numbers in parenthesis are for the chip carrier package.



FIGURE 5(c) - ELECTRICAL CIRCUIT FOR BURN-IN DYNAMIC



NOTES

1. Pin numbers in parenthesis are for the chip carrier package.



4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 9000)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.4 Conditions for Operating Life Test

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5(c) of this specification.

4.8.5 Electrical Circuits for Operating Life Tests

Circuits for use in performing the operating life test are shown in Figure 5(c) of this specification.

4.8.6 Conditions for High Temperature Storage Test

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.

**TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING**

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)			UNIT
						MIN	MAX	
1	Functional Test	-	As per Table 2	As per Table 2	-	-	-	-
3 to 4	Quiescent Current	I_{DD}	As per Table 2	As per Table 2	± 50	-	-	nA
5 to 12	Input Current Low Level	I_{IL}	As per Table 2	As per Table 2	-	-	-50	nA
13 to 20	Input Current High Level	I_{IH}	As per Table 2	As per Table 2	-	-	50	nA
21	Output Voltage Low Level NAND Output	V_{OL}	As per Table 2	As per Table 2	-	-	0.05	V
22 to 29	Output Voltage Low Level AND Output	V_{OL}	As per Table 2	As per Table 2	-	-	0.05	V
30 to 37	Output Voltage High Level NAND Output	V_{OH}	As per Table 2	As per Table 2	-	14.95	-	V
38	Output Voltage High Level AND Output	V_{OH}	As per Table 2	As per Table 2	-	14.95	-	V
39	Output Drive Current N-Channel NAND Output	I_{OL1}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
40 to 47	Output Drive Current N-Channel AND Output	I_{OL1}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
48	Output Drive Current N-Channel NAND Output	I_{OL2}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
49 to 56	Output Drive Current N-Channel AND Output	I_{OL2}	As per Table 2	As per Table 2	± 15 (1)	-	-	%

NOTES

1. Percentage of limit value if voltage is the measurement function.

**TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING (CONT'D)**

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)			UNIT
						MIN	MAX	
57 to 64	Output Drive Current P-Channel NAND Output	I_{OH1}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
65	Output Drive Current P-Channel AND Output	I_{OH1}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
66 to 73	Output Drive Current P-Channel NAND Output	I_{OH2}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
74	Output Drive Current P-Channel AND Output	I_{OH2}	As per Table 2	As per Table 2	± 15 (1)	-	-	%
75 to 82	Input Voltage Low Level (Noise Immunity) NAND Output	V_{IL1}	As per Table 2	As per Table 2	-	4.5	-	V
83 to 90	Input Voltage Low Level (Noise Immunity) AND Output	V_{IL1}	As per Table 2	As per Table 2	-	-	0.5	V
107	Input Voltage High Level (Noise Immunity) NAND Output	V_{IH1}	As per Table 2	As per Table 2	-	-	0.5	V
108	Input Voltage High Level (Noise Immunity) AND Output	V_{IH1}	As per Table 2	As per Table 2	-	4.5	-	V
111	Threshold Voltage N-Channel	V_{THN}	As per Table 2	As per Table 2	± 0.3	-	-	V
112	Threshold Voltage P-Channel	V_{THP}	As per Table 2	As per Table 2	± 0.3	-	-	V

NOTES

1. Percentage of limit value if voltage is the measurement function.

**ESC**ESA/SCC Detail Specification
No. 9201/061

PAGE 49

ISSUE 3

APPENDIX 'A'Page 1 of 1**AGREED DEVIATIONS FOR STMICROELECTRONICS (F)**

ITEMS AFFECTED	DESCRIPTION OF DEVIATION
Para. 4.2.3	Para. 9.23, High Temperature Reverse Bias Burn-in: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used. Para. 9.24, Power Burn-in: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.
Para. 4.2.4	Para. 9.21.1, Operating Life during Qualification Testing: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.
Para. 4.2.5	Para. 9.21.2, Operating Life during Lot Acceptance Testing: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.